

## P-channel 20 V, 0.0195 $\Omega$ typ., 8 A STripFET™ VII DeepGATE™ Power MOSFET in a PowerFLAT™ 2x2 package

Datasheet - production data

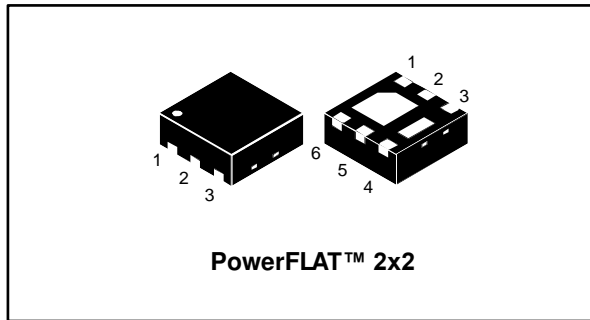
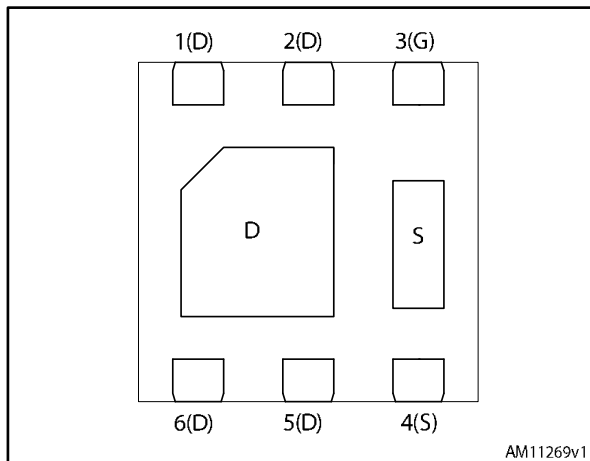


Figure 1: Internal schematic diagram



### Features

Order code	$V_{DS}$	$R_{DS(on)max}$	$I_D$
STL8P2UH7	20 V	0.0225 $\Omega$ @ 4.5 V	8 A

- Extremely low on-resistance  $R_{DS(on)}$
- Ultra logic level

### Applications


- Switching applications

### Description

This device exhibits low on-state resistance and capacitance for improved conduction and switching performance.

Table 1: Device summary

Order code	Marking	Package	Packaging
STL8P2UH7	8L2U	PowerFLAT™ 2x2	Tape and reel

-  For the P-channel Power MOSFET the actual polarity of the voltages and the current must be reversed.

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# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	20	V
$V_{GS}$	Gate-source voltage	$\pm 8$	V
$I_D$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	8	A
$I_D$	Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$	5.3	A
$I_{DM}^{(1)}$	Drain current (pulsed)	32	A
$P_{TOT}$	Total dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	2.4	W
$T_{stg}$	Storage temperature	- 55 to 150	$^\circ\text{C}$
$T_j$	Max. operating junction temperature	150	$^\circ\text{C}$

**Notes:**

<sup>(1)</sup>Pulse width limited by safe operating area

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	52	$^\circ\text{C/W}$

**Notes:**

<sup>(1)</sup>When mounted on 1inch<sup>2</sup> FR-4 board, 2 oz Cu



For the P-channel Power MOSFET the actual polarity of the voltages and the current must be reversed.

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 4: On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0, I_D = 250\ \mu A$	20			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0, V_{DS} = 20\text{ V}$			1	$\mu A$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0, V_{GS} = \pm 5\text{ V}$			$\pm 5$	$\mu A$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu A$	0.4		1	V
$R_{DS(on)}$	Static drain-source on- resistance	$V_{GS} = 4.5\text{ V}, I_D = 4\text{ A}$		0.0195	0.0225	$\Omega$
		$V_{GS} = 2.5\text{ V}, I_D = 4\text{ A}$		0.02	0.025	$\Omega$
		$V_{GS} = 1.8\text{ V}, I_D = 4\text{ A}$		0.036	0.043	$\Omega$
		$V_{GS} = 1.5\text{ V}, I_D = 4\text{ A}$		0.05	0.085	$\Omega$

**Table 5: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{GS} = 0, V_{DS} = 16\text{ V},$ $f = 1\text{ MHz}$	-	2390	-	pF
$C_{oss}$	Output capacitance		-	220	-	pF
$C_{rss}$	Reverse transfer capacitance		-	188	-	pF
$Q_g$	Total gate charge	$V_{DD} = 16\text{ V}, I_D = 8\text{ A},$ $V_{GS} = 4.5\text{ V}$	-	22	-	nC
$Q_{gs}$	Gate-source charge		-	4.2	-	nC
$Q_{gd}$	Gate-drain charge		-	3.6	-	nC



For the P-channel Power MOSFET the actual polarity of the voltages and the current must be reversed.

**Table 6: Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 16\text{ V}, I_D = 8\text{ A},$ $R_G = 1\ \Omega, V_{GS} = 4.5\text{ V}$	-	12.5	-	ns
$t_r$	Rise time		-	30.5	-	ns
$t_{d(off)}$	Turn-off delay time		-	128	-	ns
$t_f$	Fall time		-	84.5	-	ns

Table 7: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		8	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		32	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0, I_{SD} = 1 \text{ A}$	-		1	V
$t_{rr}$	Reverse recovery time	$V_{DD} = 16 \text{ V}$ $di/dt = 100 \text{ A}/\mu\text{s}$ , $I_{SD} = 1 \text{ A}$	-	15.8		ns
$Q_{rr}$	Reverse recovery charge		-	5.9		nC
$I_{RRM}$	Reverse recovery current		-	0.7		A

**Notes:**

<sup>(1)</sup>Pulse width limited by safe operating area.

<sup>(2)</sup>Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%



For the P-channel Power MOSFET the actual polarity of the voltages and the current must be reversed.

## 2.1 Electrical characteristics (curves)

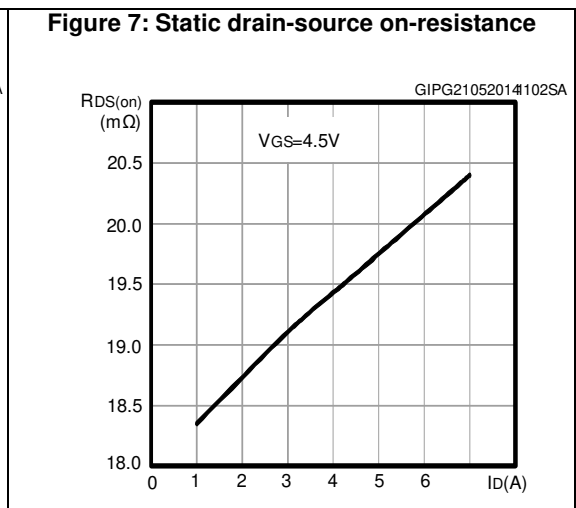
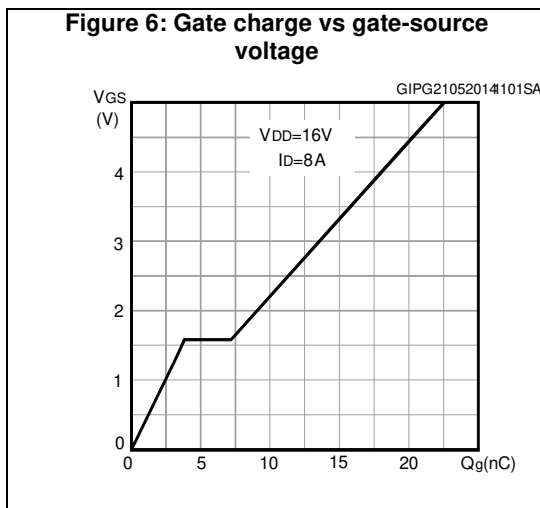
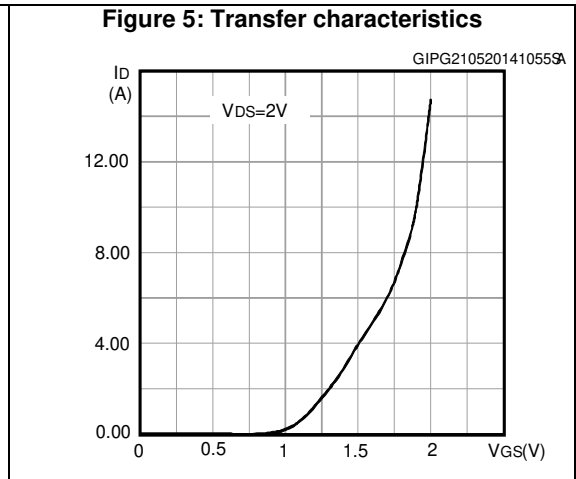
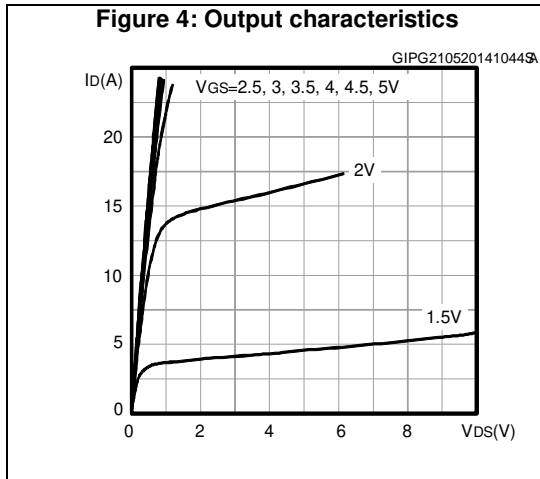
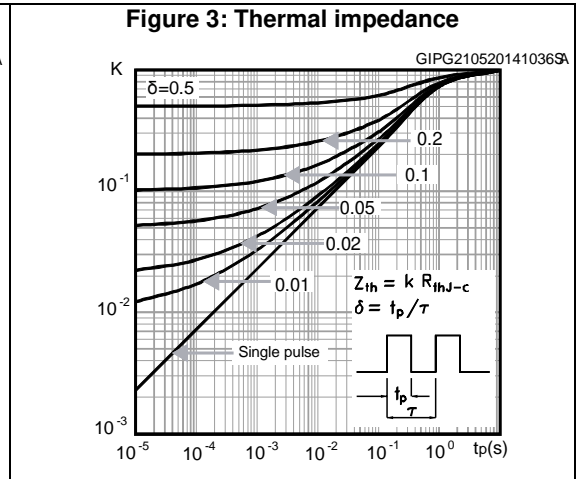
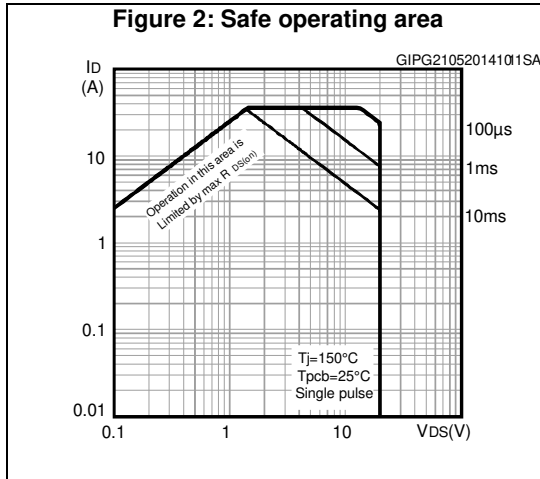


Figure 8: Capacitance variations

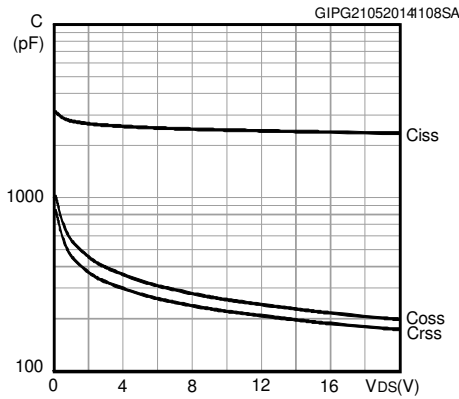


Figure 9: Normalized gate threshold voltage vs temperature

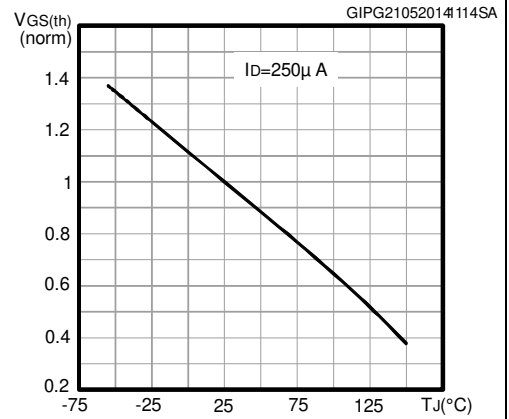


Figure 10: Normalized on-resistance vs temperature

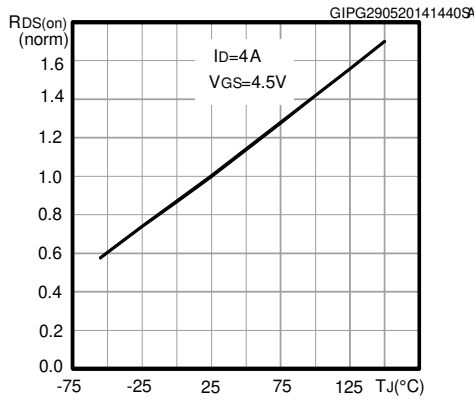


Figure 11: Normalized V(BR)DSS vs temperature

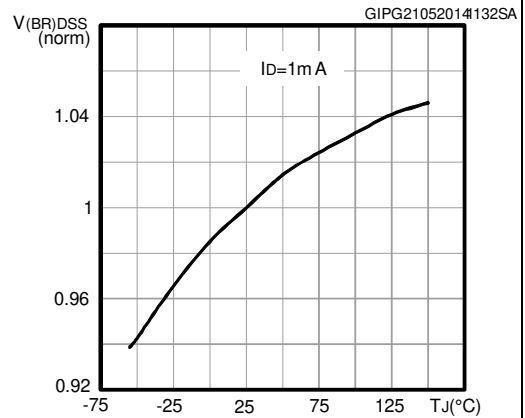
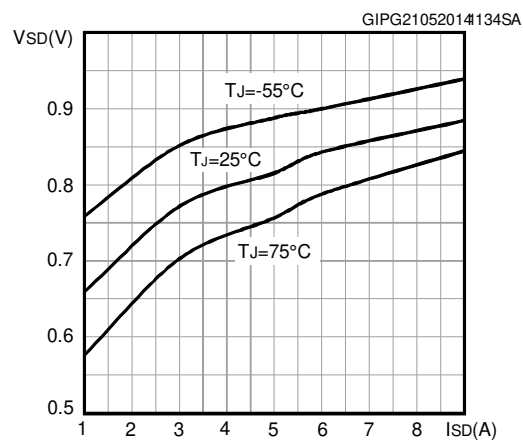
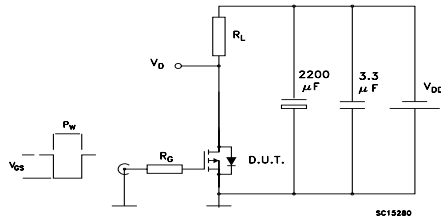


Figure 12: Source-drain diode forward characteristics

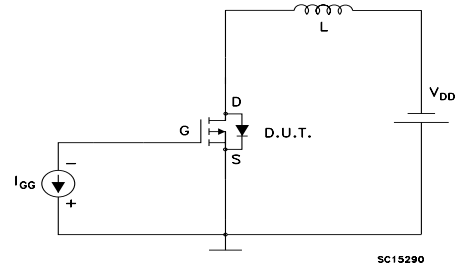


### 3 Test circuits

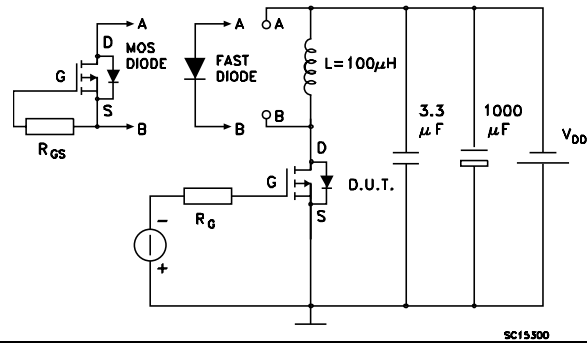
**Figure 13: Switching times test circuit for resistive load**



**Figure 14: Gate charge test circuit**



**Figure 15: Test circuit for inductive load switching and diode recovery times**





## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

### 4.1 PowerFLAT™ 2x2 package mechanical data

Figure 16: Drawing dimension PowerFLAT™ 2 x 2

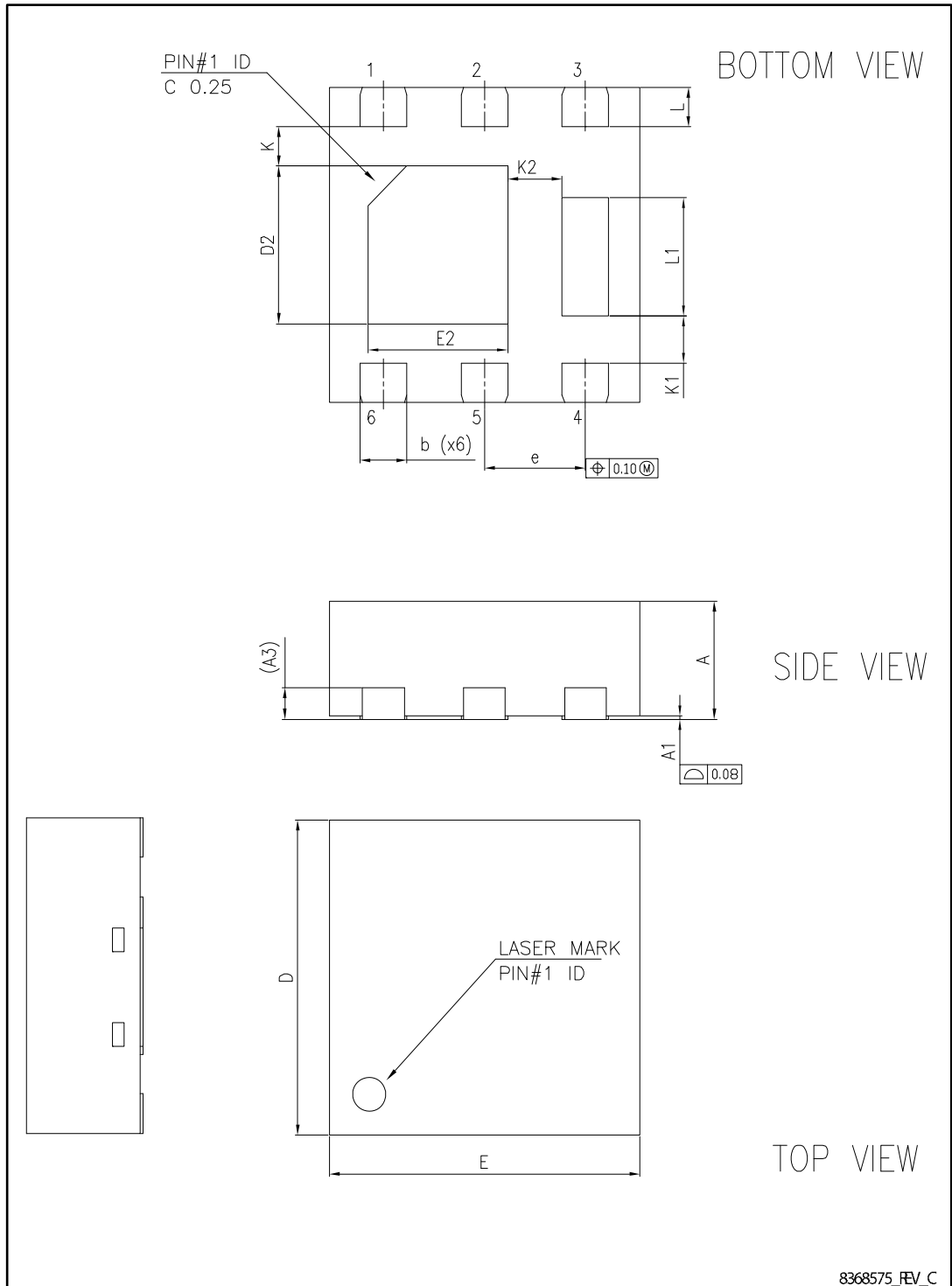


Table 8: PowerFLAT™ 2 x 2 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
A3		0.20	
b	0.25	0.30	0.35
D	1.90	2.00	2.10
E	1.90	2.00	2.10
D2	0.90	1.00	1.10
E2	0.80	0.90	1.00
e	0.55	0.65	0.75
K	0.15	0.25	0.35
K1	0.20	0.30	0.40
K2	0.25	0.35	0.45
L	0.20	0.25	0.30
L1	0.65	0.75	0.85



## 5 Revision history

**Table 9: Document revision history**

Date	Revision	Changes
20-Aug-2013	1	First release.
04-Jun-2014	2	Document status promoted from preliminary data to production data Modified: title Modified: $R_{DS(on)}$ max value in cover page Modified: $R_{DS(on)}$ (typical and maximum) values in <a href="#">Table 4: "On /off states"</a> Modified: the entire typical values in <a href="#">Table 5: "Dynamic"</a> , <a href="#">Table 6: "Switching times"</a> and <a href="#">Table 7: "Source drain diode"</a> Added <a href="#">Section 8.1: "Electrical characteristics (curves)"</a> Minor text changes

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